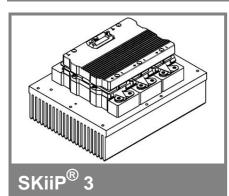
## SKiiP 1513GB122-3DL



2-pack-integrated intelligent Power System

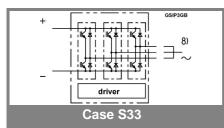
#### **Power Section**

SKiiP 1513GB122-3DL

Data

#### **Power section features**

- SKiiP technology inside
- SPT (Soft Punch Trough) IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP<sup>®</sup> 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized File no. E63532
- with assembly of suitable MKP capacitor per terminal
- AC connection busbars must be connected by the user; copper busbars available on request



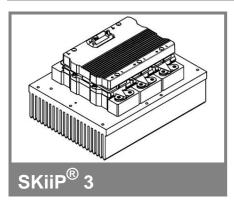
Absolute	Maximum Ratings	$\Gamma_s$ = 25 °C unless otherwise specified						
Symbol  Conditions		Values	Units					
IGBT								
V <sub>CES</sub>		1200	V					
V <sub>CC</sub> <sup>1)</sup>	Operating DC link voltage	900	V					
V <sub>GES</sub>		± 20	V					
Ι <sub>C</sub>	T <sub>s</sub> = 25 (70) °C	1500 (1125)	А					
Inverse o	Inverse diode							
$I_F = -I_C$	T <sub>s</sub> = 25 (70) °C	1340 (1020)	А					
I <sub>FSM</sub>	T <sub>j</sub> = 150 °C, t <sub>p</sub> = 10 ms; sin	10200	A					
I²t (Diode)	Diode, T <sub>j</sub> = 150 °C, 10 ms	520	kA²s					
T <sub>j</sub> , (T <sub>stg</sub> )		- 40 + 150 (125)	°C					
V <sub>isol</sub>	rms, AC, 1 min, main terminals to heat sink	3000	V					
I <sub>AC-terminal</sub>	per AC terminal, rms, T <sub>s</sub> = 70 °C,	400	А					
	T <sub>terminal</sub> <115 °C							

<b>Characteristics</b> $T_s = 25 \degree C$ unless otherwise spectrum $T_s = 25 \degree C$ unl						
Symbol Conditions		min.	typ.	max.	Units	
IGBT						
V <sub>CEsat</sub>	$I_{C}$ = 900 A, $T_{j}$ = 25 (125) °C; measured at terminal		2,3 (2,5)	2,6	V	
V <sub>CEO</sub>	T <sub>i</sub> = 25 (125) °C; at terminal		1,1 (1)	1,3 (1,2)	v	
r <sub>CE</sub>	T <sub>i</sub> = 25 (125) °C; at terminal		1,3 (1,7)	1,5 (1,9)	mΩ	
I <sub>CES</sub>	$V_{GE} = 0 V, V_{CE} = V_{CES},$ T <sub>i</sub> = 25 (125) °C		3,6 (108)		mA	
E <sub>on</sub> + E <sub>off</sub>	I <sub>C</sub> = 900 A, V <sub>CC</sub> = 600 V		270		mJ	
	T <sub>j</sub> = 125 °C, V <sub>CC</sub> = 900 V		476		mJ	
R <sub>CC+EE</sub>	terminal chip, T <sub>i</sub> = 25 °C		0,17		mΩ	
L <sub>CE</sub>	top, bottom		4		nH	
C <sub>CHC</sub>	per phase, AC-side		5,1		nF	
Inverse	diode				•	
$V_F = V_{EC}$	$I_F = 900 \text{ A}, T_j = 25 (125) ^{\circ}\text{C}$ measured at terminal		1,95 (1,7)	2,1	V	
V <sub>TO</sub>	T <sub>i</sub> = 25 (125) °C		1,1 (0,8)	1,2 (0,9)	V	
r <sub>T</sub>	T <sub>i</sub> = 25 (125) °C		0,9 (1)	1 (1,2)	mΩ	
E <sub>rr</sub>	I <sub>C</sub> = 900 A, V <sub>CC</sub> = 600 V		72		mJ	
	T <sub>j</sub> = 125 °C, V <sub>CC</sub> = 900 V		92		mJ	
Mechan	ical data				•	
M <sub>dc</sub>	DC terminals, SI Units	6		8	Nm	
M <sub>ac</sub>	AC terminals, SI Units	13		15	Nm	
w	SKiiP <sup>®</sup> 3 System w/o heat sink		2,4		kg	
w	heat sink		7,5		kg	
Thermal characteristics (PX 16 heat sink with fan SKF 16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)						
R <sub>th(j-s)l</sub>	per IGBT			0,02	K/W	

R <sub>th(j-s)I</sub>	per IGB	Т					0,02	K/W	
R <sub>th(j-s)D</sub>	per diod	е					0,038	K/W	
Z <sub>th</sub>	R <sub>i</sub> (mK/V	R <sub>i</sub> (mK/W) (max. values)				tau <sub>i</sub> (s)			
	1	2	3	4	1	2	3	4	
Z <sub>th(j-r)I</sub>	3,4	9,6	7	0	363	0,18	0,04	1	
Z <sub>th(j-r)D</sub>	12	12	18	20	30	5	0,25	0,04	
Z <sub>th(r-a)</sub>	2,1	20	5,5	1,4	210	85	11	0,4	

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# SKiiP 1513GB122-3DL



### 2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1513GB122-3DL

Data

### Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protection against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings	a = 25 °C unless otherwise specified		
Symbol	Conditions	Values	Units	
V <sub>S2</sub>	unstabilized 24 V power supply	30	V	
V <sub>i</sub>	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/µs	
V <sub>isollO</sub>	input / output (AC, rms, 2)	3000	V	
VisoIPD	partial discharge extinction voltage, rms, $Q_{PD} \leq 10 \text{ pC}$ ;	1170	V	
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2 s)	1500	V	
f <sub>sw</sub>	switching frequency	10	kHz	
f <sub>out</sub>	output frequency for I <sub>peak(1)</sub> =I <sub>C</sub>	10	kHz	
T <sub>op</sub> (T <sub>stg</sub> )	operating / storage temperature	- 40 + 85	°C	

Characte	eristics	(T <sub>a</sub>			= 25 °C)
Symbol	Conditions	min.	typ.	max.	Units
V <sub>S2</sub>	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 24 V	278+29*f/	/kHz+0,0001	15*(I <sub>AC</sub> /A) <sup>2</sup>	mA
V <sub>iT+</sub>	input threshold voltage (High)			12,3	V
V <sub>iT-</sub>	input threshold voltage (Low)	4,6			V
R <sub>IN</sub>	input resistance		10		kΩ
CIN	input capacitance		1		nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,3		μs
t <sub>d(off)IO</sub>	input-output turn-off propagation time		1,3		μs
t <sub>pERRRESET</sub>	error memory reset time		9		μs
t <sub>TD</sub>	top / bottom switch interlock time		3,3		μs
I <sub>analogOUT</sub>	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1500		A
I <sub>s1out</sub>	max. load current			50	mA
I <sub>TRIPSC</sub>	over current trip level				
	$(I_{analog} OUT = 10 V)$		1875		А
T <sub>tp</sub>	over temperature protection	110		120	°C
UDCTRIP	U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V);		not implemente	d	V
	(option for GB types)				

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